

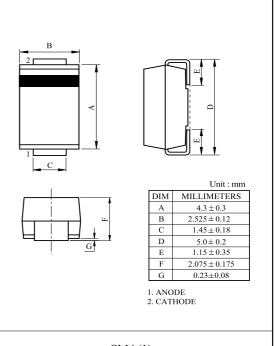
SEMICONDUCTOR TECHNICAL DATA

GN1G

Surface Mount Glass Passivated Rectifier

## FEATURES

- Plastic package has Underwriters Laboratory flammability Classification 94V-0.
- For surface mounted aplications.
- Low profile package.
- $\cdot$  Built-in strain relief, ideal for automated placement.
- $\cdot$  Glass passivated chip junction.
- $\cdot$  High temperature soldering guaranteed
- : 250 /10 seconds at terminals.



## MAXIMUM RATING (Ta=25)

MAXIMUM RATING (Ta=25)				$\begin{array}{c c c c c c c c c c c c c c c c c c c $
CHARACTERISTIC	SYMBOL	RATING	UNIT	D 5.0±0.2   E 1.15±0.35
Repetitive peak reverse voltage	V <sub>RRM</sub>	400	V	$\begin{array}{ccc} F & 2.075 \pm 0.175 \\ \hline G & 0.23 \pm 0.08 \end{array}$
RMS voltage	V <sub>RMS</sub>	280	V	1. ANODE 2. CATHODE
DC blocking voltage	V C	400	V	
Average forward rectified current (see fig.1)	Í <sub>F(AV)</sub>	1	А	SMA(1)
Peak forward surge current 8.7 .s cingle		YN		
half sine-wave superimpc id n at	I <sub>FSM</sub>		A	
load (JEDEC Method) T <sub>L</sub> =110				
Operating Junction and	7 7 0	-55~150		Marking Cathode Mark
Storage Temperature Range	, ığ	- 15-150		Marking Cathode Mark
		71/7		Type Name
		~	ale.	Z 40 Lot No.

## ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC 5		SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Forward voltage		V <sub>F</sub>	I <sub>F</sub> =1A	-	-	1.1	V
Leakage current	Ta=25	– I <sub>R</sub>	V <sub>RRM</sub> =400V	-	-	1.0	μA
	Ta=125		V <sub>RRM</sub> -400V	-	-	50	
everse recovery time t <sub>rr</sub>		$I_F=0.5A, I_R=1.0A$	-	1.8	-	μS	
Junction capacitance C <sub>J</sub>		CJ	V <sub>R</sub> =4.0V, f=1MHz	-	12	-	pF
Thermal resistance		R <sub>th</sub> (A) (Note1)	Junction to ambient	-	-	75	/W
		R <sub>th</sub> (L)	Junction to lead	-	-	27	

Note 1) Thermal resistance from junction to ambient and from junction to lead mounted

on P.C.B with  $(5.0 \times 5.0 \text{mm})$  copper pads.

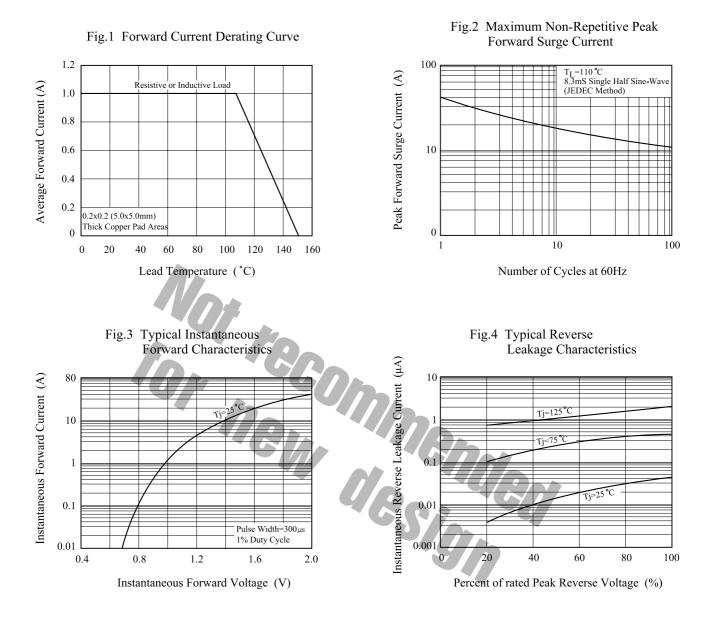


Fig.5 Typical Junction Capacitance

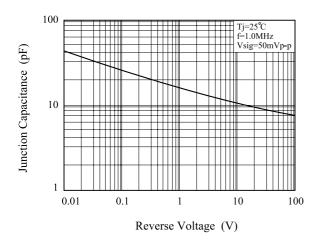


Fig.6 Transient Thermal Impedance

